

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE30P12S uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -30V, I_{D} = -12A$

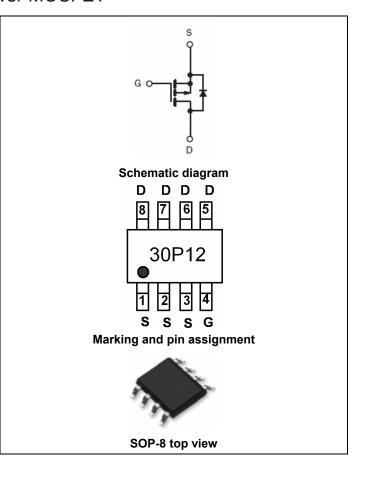
 $R_{DS(ON)}$ < 25m Ω @ V_{GS} =-4.5V

 $R_{DS(ON)}$ < 16m Ω @ V_{GS} =-10V

- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
30P12	NCE30P12S	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

5 \ 7	,		
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	-12	Α
Drain Current-Pulsed (Note 1)	I _{DM}	-48	Α
Maximum Power Dissipation	P _D	3	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	41.67	°C/W

Electrical Characteristics (T_A=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						



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NCE30P12S

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	•					
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA	-1	-1.5	-3	V
Davis Course On Otata Davistance	_	V _{GS} =-10V, I _D =-10A	-	11.5	15	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-7A	-	18	25	mΩ
Forward Transconductance	g FS	V _{DS} =-10V,I _D =-10A	20	-	-	S
Dynamic Characteristics (Note4)	•					
Input Capacitance	C _{lss}	\/ 45\/\\ 0\/	-	1750	-	PF
Output Capacitance	Coss	V_{DS} =-15V, V_{GS} =0V, F=1.0MHz	-	215	-	PF
Reverse Transfer Capacitance	C _{rss}	7		180	-	PF
Switching Characteristics (Note 4)	•					
Turn-on Delay Time	t _{d(on)}		-	9	-	nS
Turn-on Rise Time	t _r	V _{DD} =-15V, ID=-10A,	-	8	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =-10V, R_{GEN} =1 Ω	-	28	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg		-	24	1	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-15V,I _D =-10A,V _{GS} =-10V	-	3.5	-	nC
Gate-Drain Charge	Q_{gd}		-	6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-2A	-	-	-1.2	V

Notes:

- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

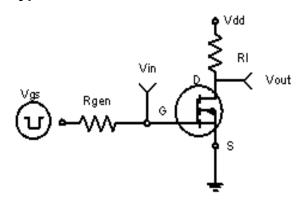
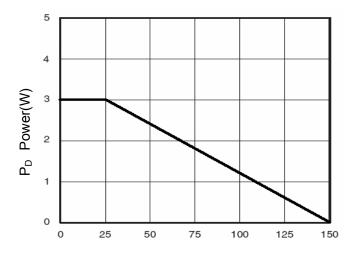


Figure 1:Switching Test Circuit



 T_J -Junction Temperature(°C) Figure 3 Power Dissipation

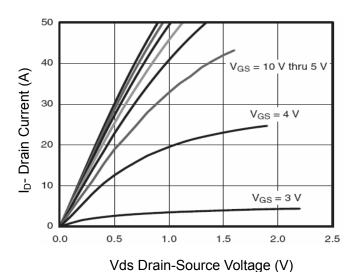


Figure 5 Output Characteristics

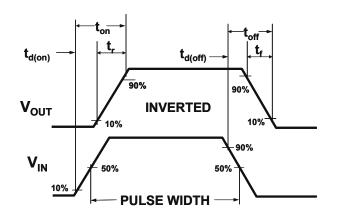


Figure 2:Switching Waveforms

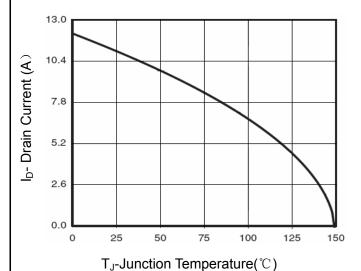


Figure 4 Drain Current

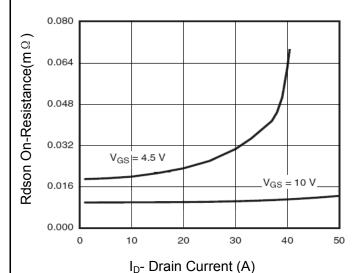
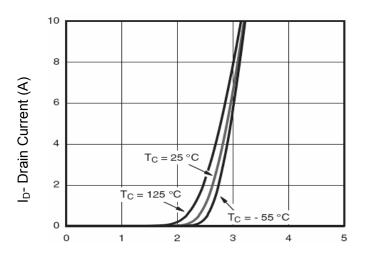


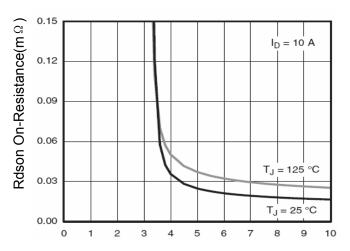
Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)

Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

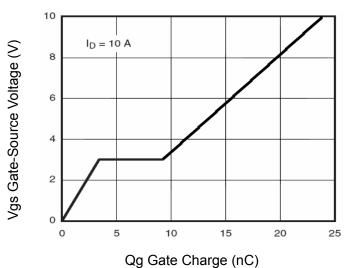
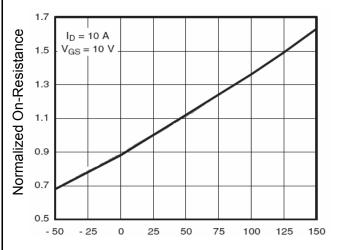
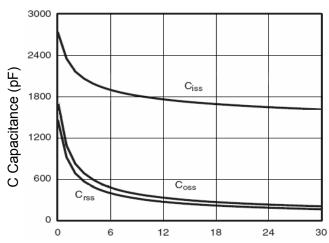


Figure 11 Gate Charge



 T_J -Junction Temperature($^{\circ}$ C)





Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

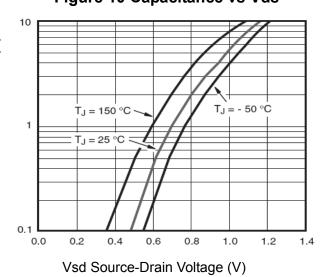
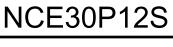
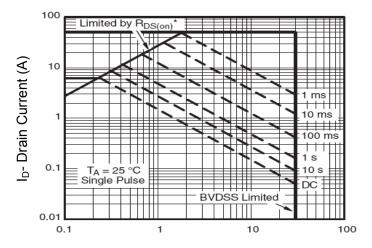


Figure 12 Source- Drain Diode Forward

Is- Reverse Drain Current (A)







Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

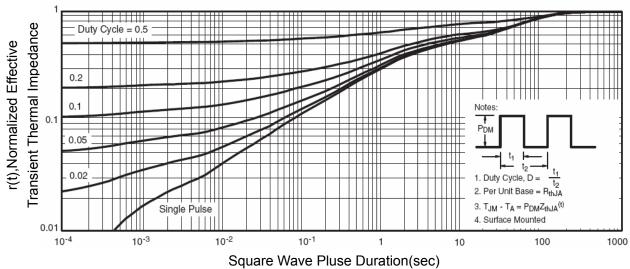
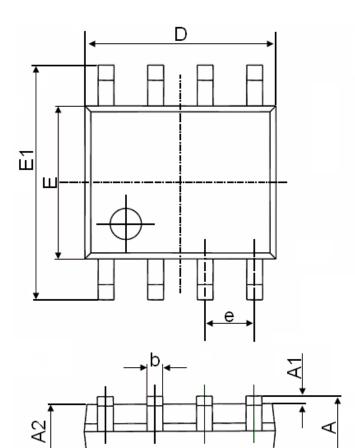


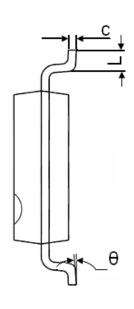
Figure 14 Normalized Maximum Transient Thermal Impedance



NCE30P12S

SOP-8 Package Information





Comphal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	(BSC)	0.050(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



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Pb Free Product
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